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[54] **METHOD AND DEVICE FOR INITIATING A MEMORY ARRAY DURING POWER UP**

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[57] **ABSTRACT**

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The present invention is a device and method for a semiconductor array which attempts to ensure that, during power up, a reference cell becomes valid after one or more data cells. The array includes at least one data cell, at least one cell common line to which the data cell is connected, at least one reference cell, a reference common line to which the reference cell is connected and a voltage differentiator. The voltage differentiator is connected to the cell and reference common lines and receives a powering-up power supply voltage from a power supply. The voltage differentiator provides a reference voltage to the reference common line and a cell voltage to the at least one cell common line, wherein the reference voltage is lower than the cell voltage by a predetermined voltage gap.

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[22] Filed: **Feb. 4, 1999**

[51] Int. Cl.⁷ **G11C 7/00**

[52] U.S. Cl. **365/226; 365/210**

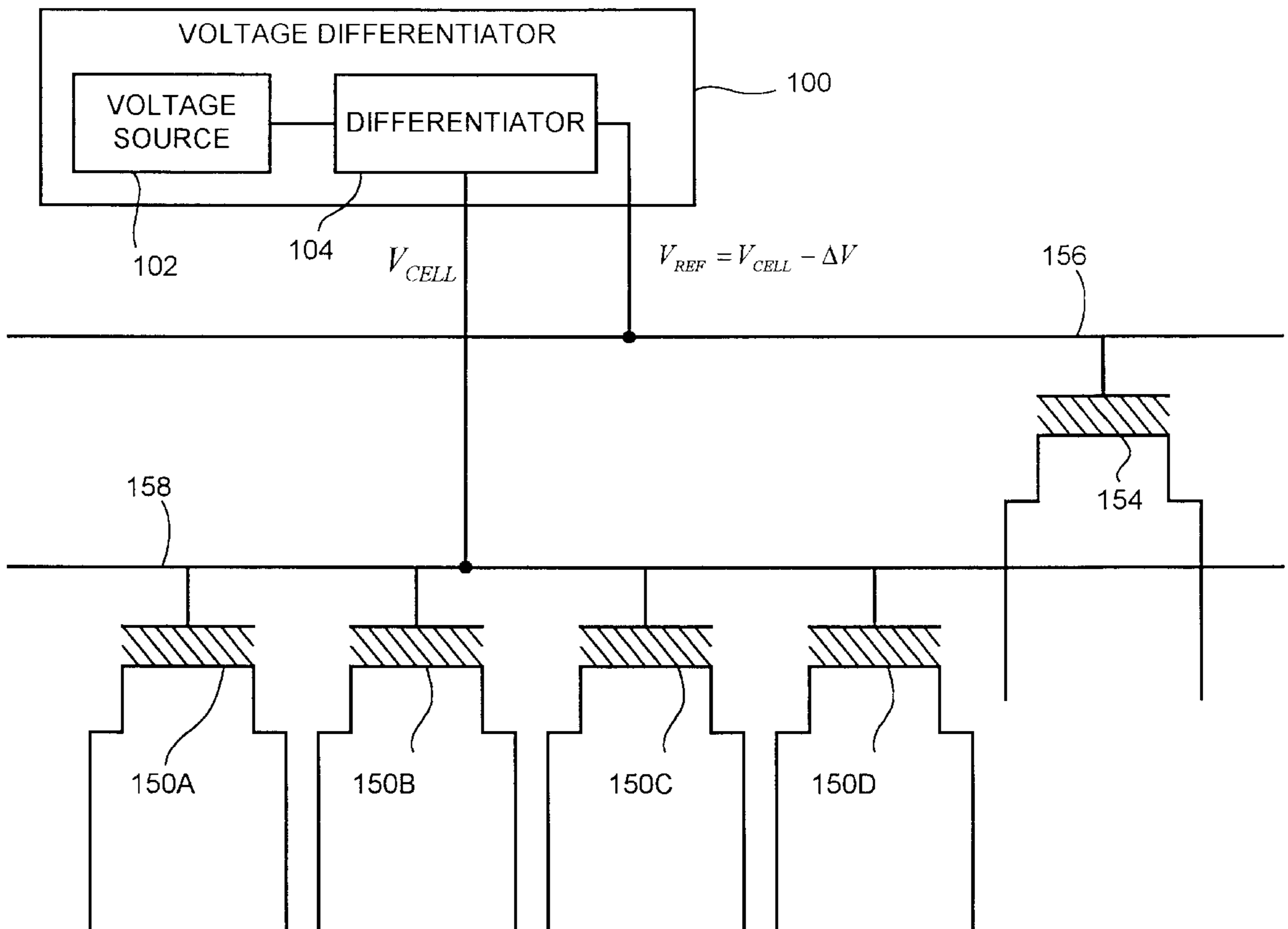
[58] Field of Search **365/226, 189.07, 365/210, 189.01**

[56] **References Cited**

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14 Claims, 9 Drawing Sheets



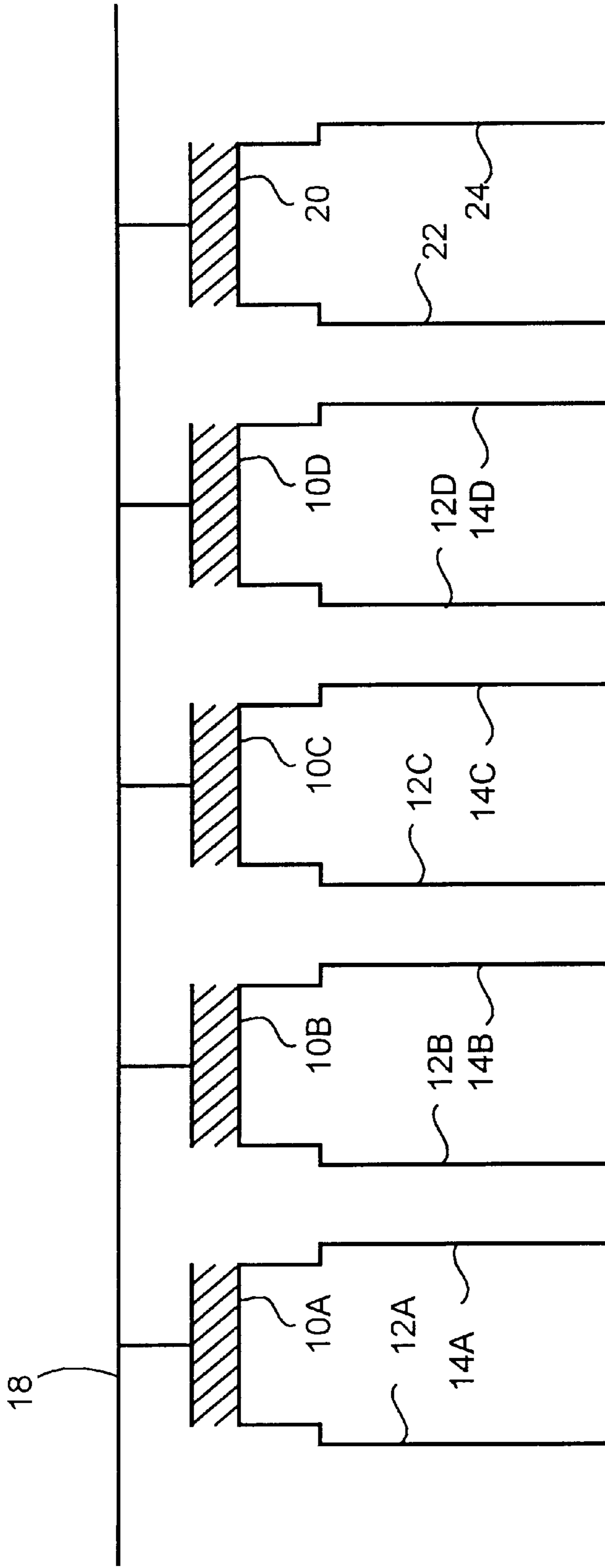


FIG. 1
PRIOR ART

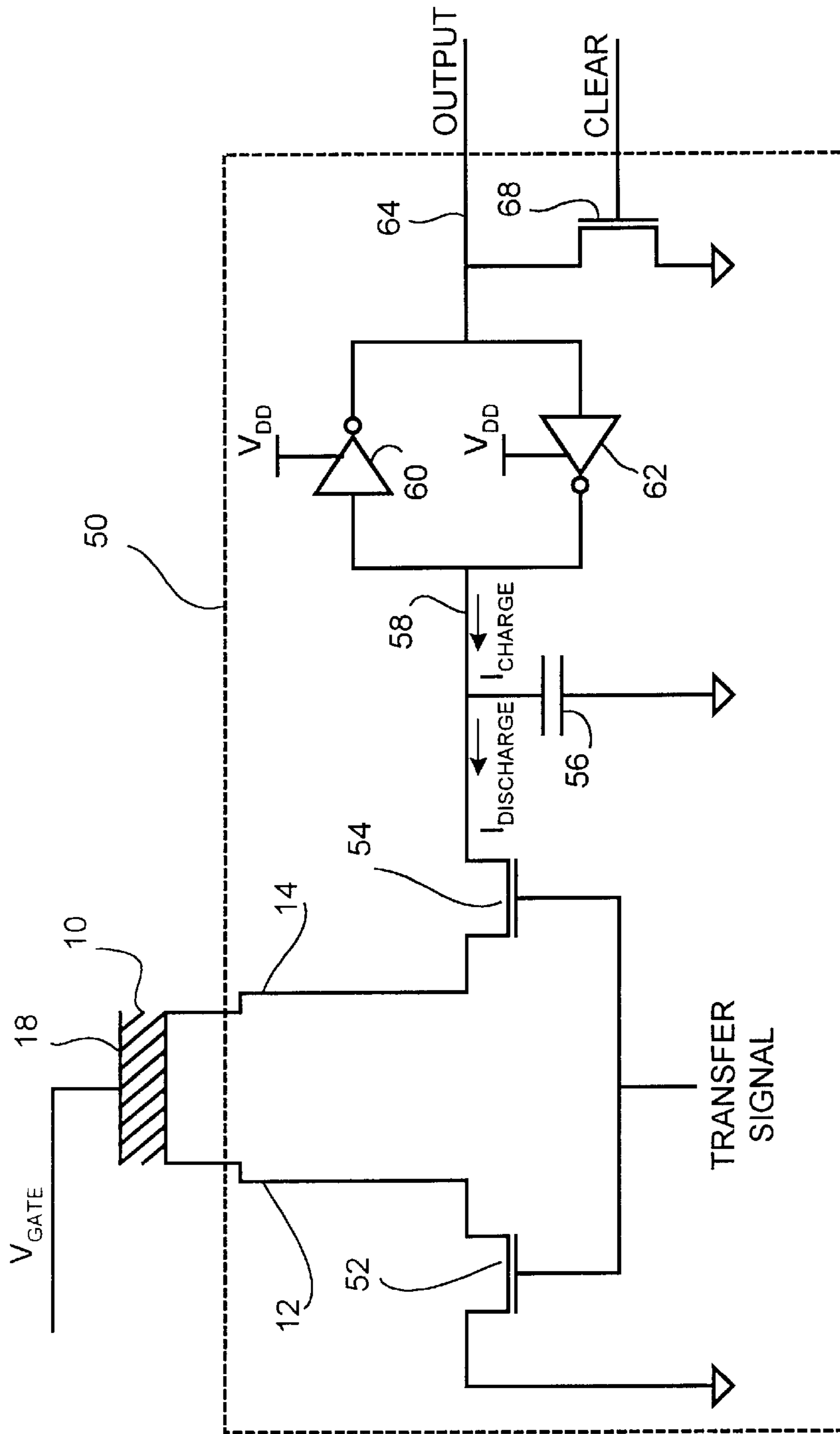


FIG. 2
PRIOR ART

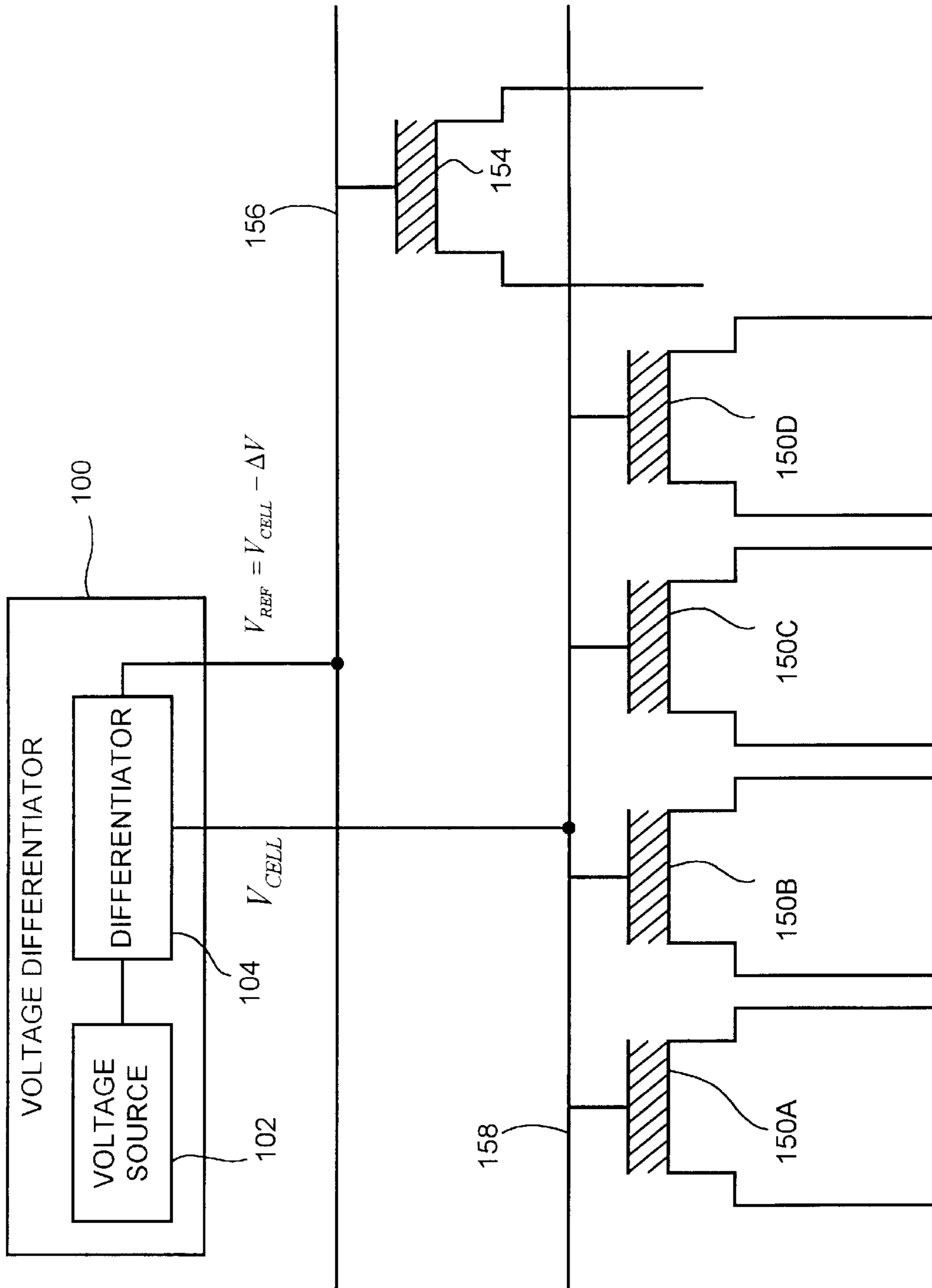


FIG. 3

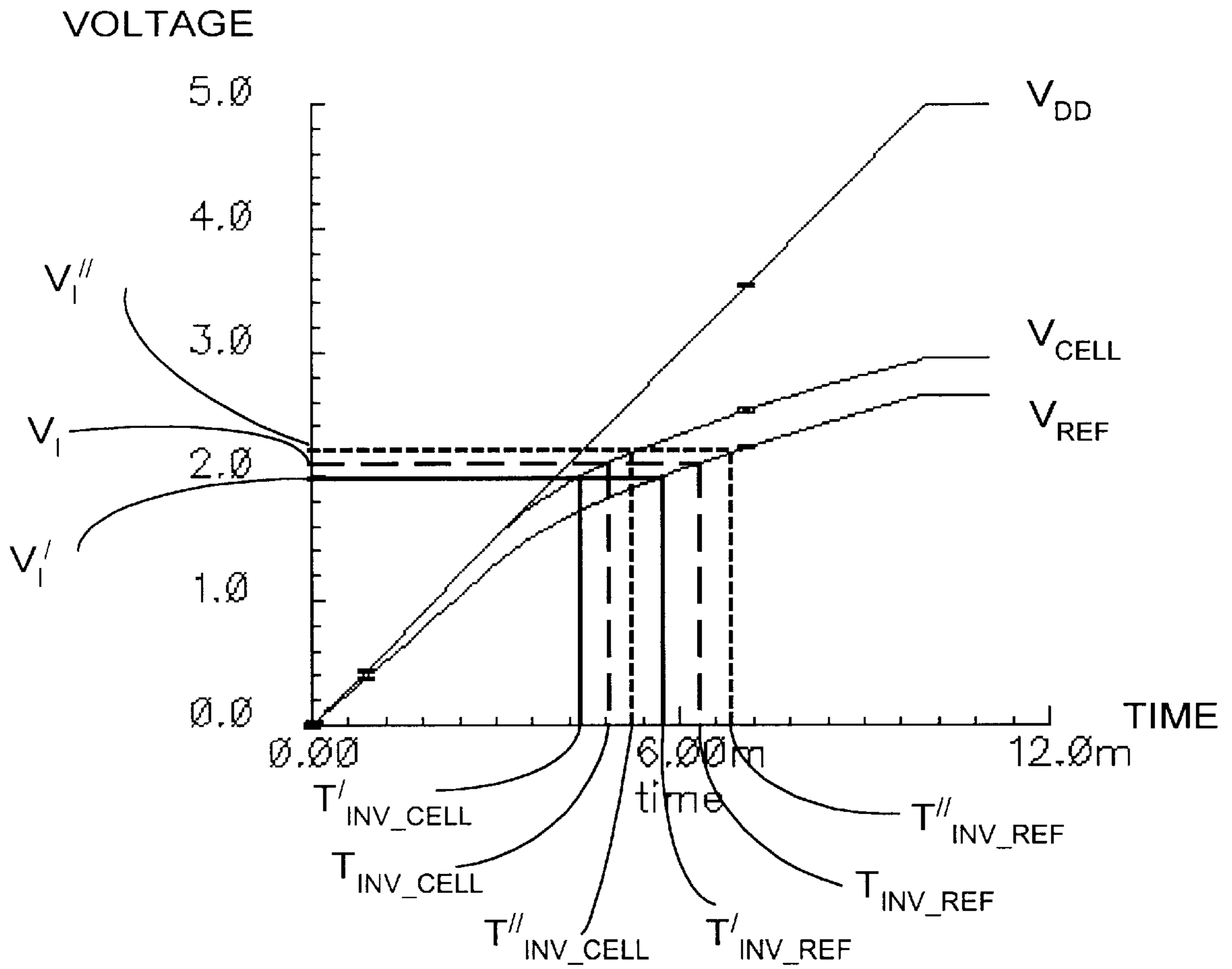


FIG. 4A

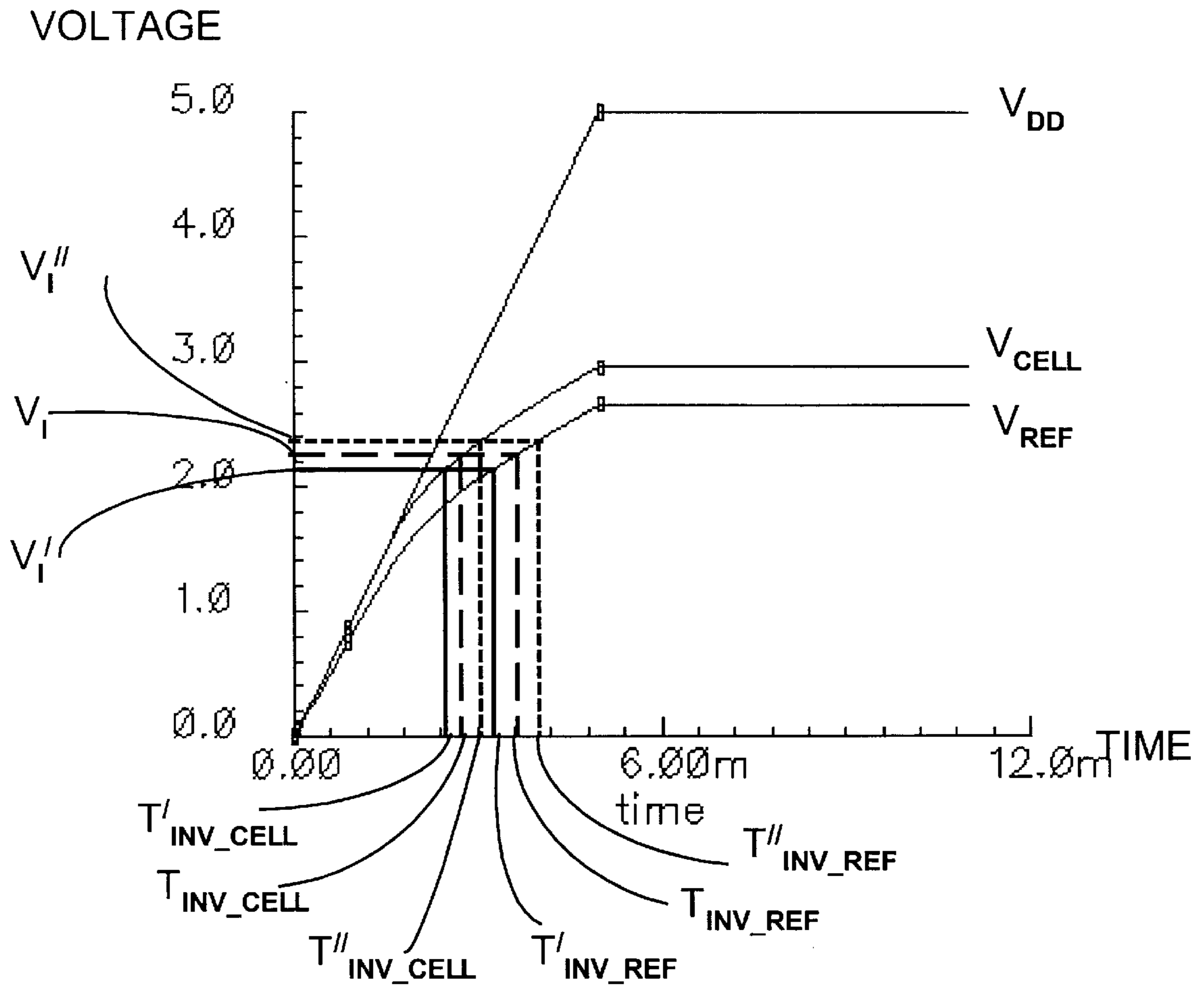


FIG. 4B

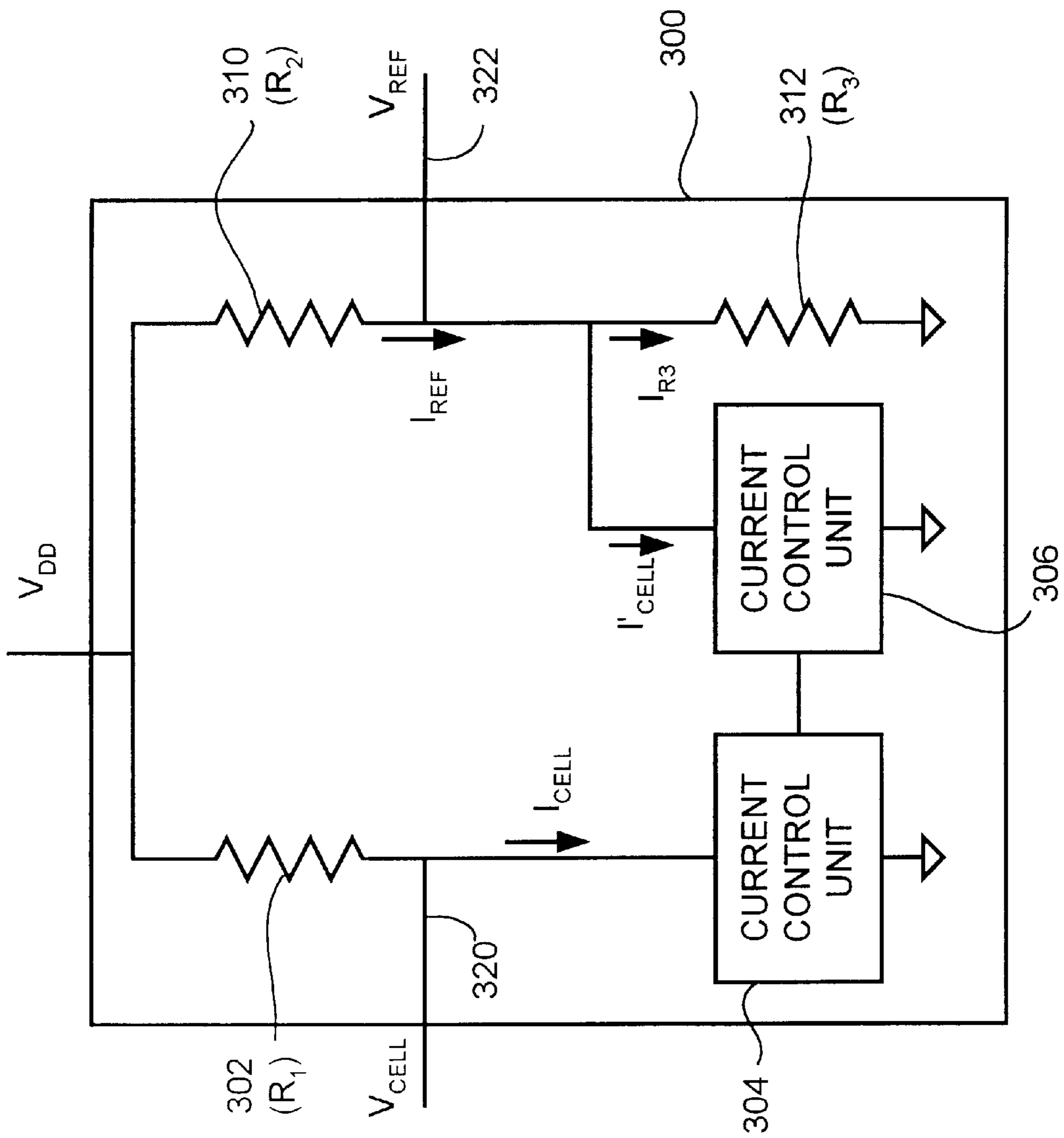


FIG. 5

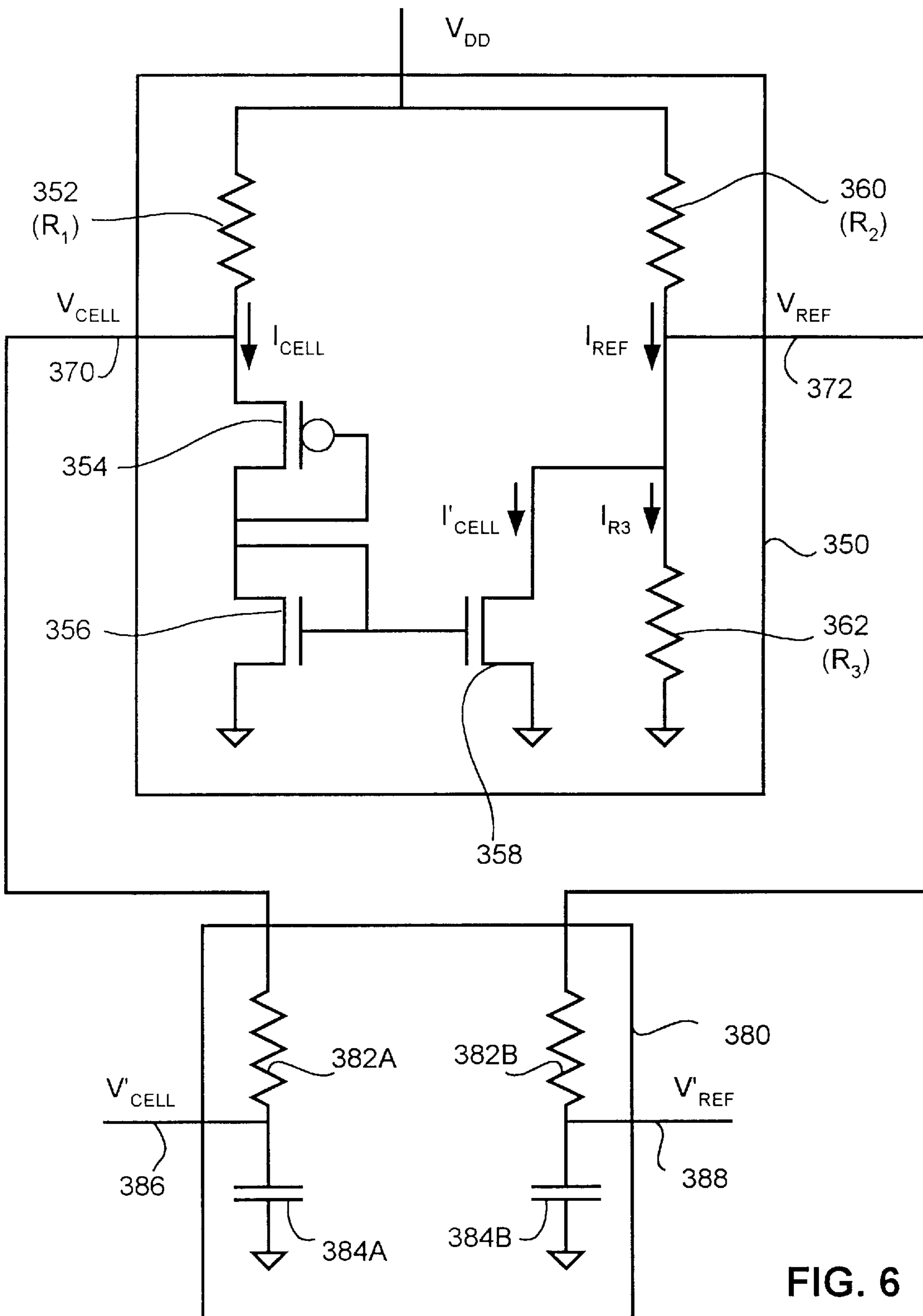
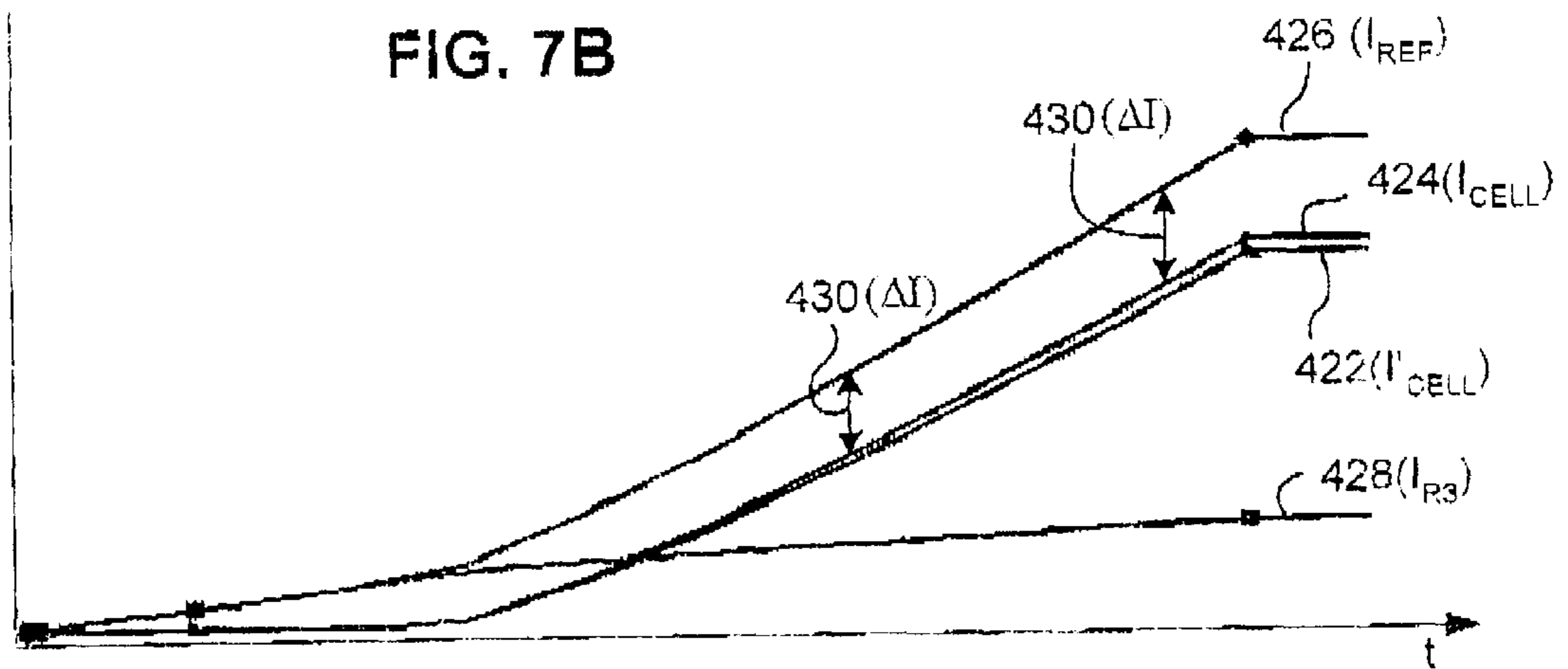
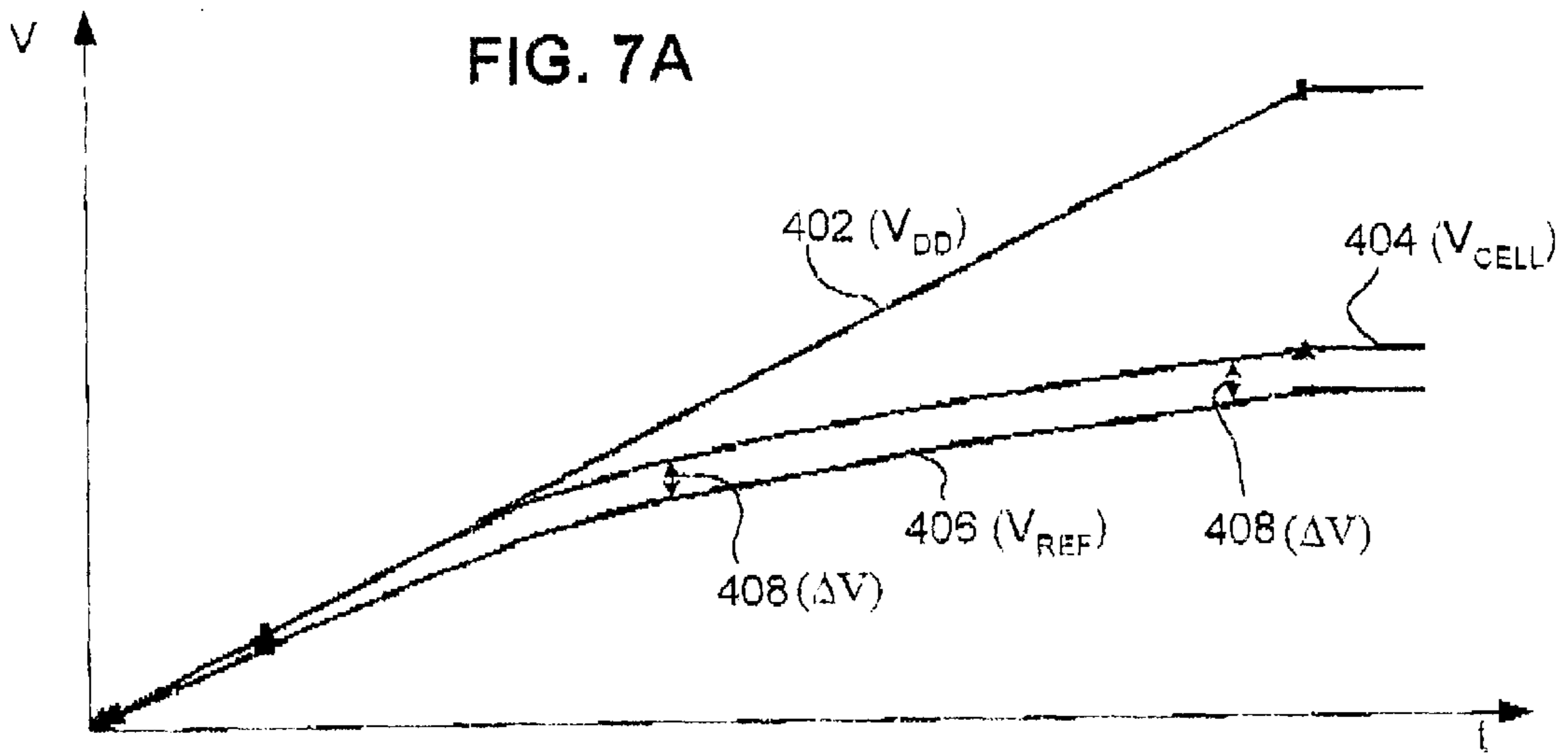


FIG. 6



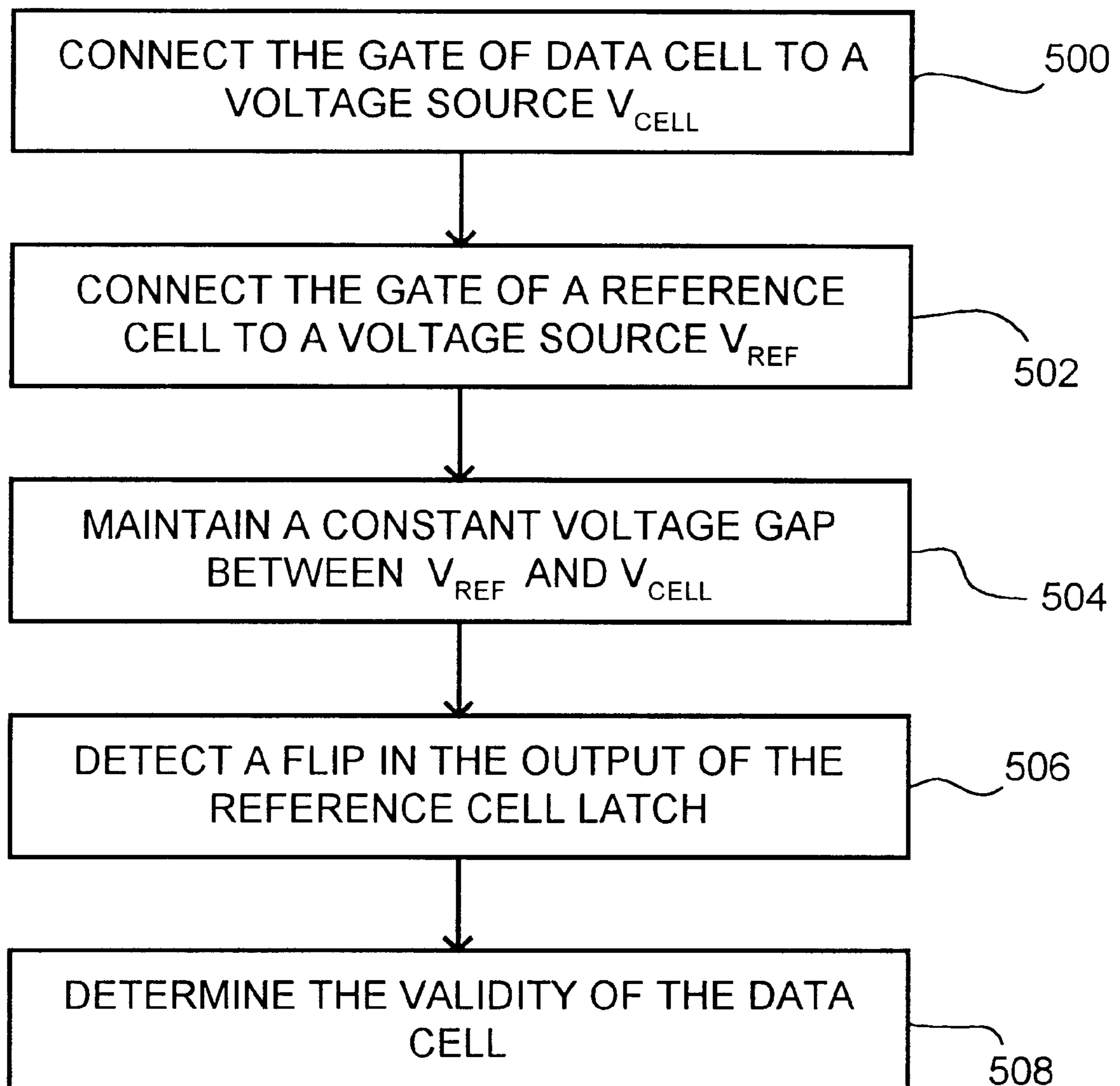


FIG. 8

METHOD AND DEVICE FOR INITIATING A MEMORY ARRAY DURING POWER UP

FIELD OF THE INVENTION

The present invention relates to methods and devices for initiating a memory cell array, in general, and to methods and devices for determining the time period in which the data of a memory cell becomes valid, in particular.

BACKGROUND OF THE INVENTION

Latch based, non-volatile memory devices are known in the art. The basic element of such a device includes a non-volatile memory cell and a latch unit which is connected thereto. The latch unit provides an indication of the data which is stored in the cell by providing an output electrical signal.

When the memory device is initiated (such as during power-up), it is necessary to determine the time period after which the data contained therein is valid for retrieval. It is noted that during the initiation stage, the variations in the behavior of the device, due to its structure, the voltage levels provided thereto, as well as other environmental conditions, are not stable and induce considerable constraints over the process of validation of the content of the cells.

Reference is now made to FIG. 1 which is a schematic illustration of a plurality of data cells, generally referenced **10**, and a reference cell, generally referenced **20**, known in the art. The gate ends of data cells **10A**, **10B**, **10C** and **10D** and reference cell **20** are connected to a common line **18**. Each of the data cells **10A**, **10B**, **10C** and **10D** are connected to a pair of terminal lines **12A–14A**, **12B–14B**, **12C–14C** and **12D–14D**, respectively. Reference cell **20** is connected to terminal lines **22** and **24**.

Reference is further made to FIG. 2 which is a schematic illustration of a memory cell and latch device, known in the art. Latch device **50** includes two switching transistors **54** and **52**, a capacitor **56**, a latch formed of two inverters **60** and **62** (both powered by a power supply Vdd) and a transistor **68**. The device **50** is connected to a memory cell, having a source **14**, a drain **12** and a gate **18**.

Inverter **60** is connected to capacitor **56**, via line **58**, and to the source of transistor **68**, via line **64**, facing the transistor **68**. Inverter **62** is connected to capacitor **56**, via line **58**, and to the source of transistor **68**, via line **64**, facing the capacitor **56**.

Switching transistor **52** is connected between the drain **12** of the memory cell and the ground. Switching transistor **54** is connected between source **14** of the memory cell and a line **58**. Both switching transistors are activated by the same transfer signal which is provided by the system (not shown).

The capacitor **56** is further connected to the ground. The drain of the transistor **68** is also connected to the ground. The gate of the transistor **68** is connected to a voltage source (not shown) which is used to “clear” the device **50**. The memory cell gate is connected to common line **18**.

As the gate of the transistor **68** receives a “clear” signal, it connects line **64** to the ground, thereby decreasing the voltage level exhibited on line **64**. As a result, inverter **62** inverts a low potential on line **64** to a high potential on line **58** and charges the capacitor **56**. The current which is provided by inverter **62** is denoted I_{CHARGE} .

When switching transistors **52** and **54** are activated, cell **10** is connected to the rest of the device. As the gate voltage V_{GATE} of cell **10** rises, cell **10** conducts electrical current ($I_{DISCHARGE}$) according to its programmed state, which is

defined by its threshold voltage V_T . A programmed cell is characterized by a high threshold voltage and, as a result, when V_{GATE} is applied thereto, the programmed cell hardly conducts charge ($I_{DISCHARGE} \ll I_{CHARGE}$). An erased cell, on the other hand, is characterized by a low threshold voltage which produces significant current ($I_{DISCHARGE} > I_{CHARGE}$) when V_{GATE} is applied to the cell.

An erased cell, being able to conduct large currents, discharges the capacitor **56** to the ground, thereby yielding a ground potential over line **58**. At this stage, the inverter **60** inverts the low potential over line **58** to high potential over line **64**.

On the other hand, a programmed cell, being able to conduct only low currents, does not conduct enough current to discharge the capacitor **56** to the ground. Accordingly, the potential over line **58** remains high. At this stage, the potential over line **58** remains high and the inverter **60** maintains a low potential over line **64**. Thus, the output of device **50** remains unchanged for a programmed cell.

It is noted that the inversion time $T_{INVERSION}$ which an erased cell takes to invert the output of device **50**, after which the data of the output signal is considered “valid”, varies for different possible values of the threshold voltage V_T of the cell, the profile of V_{GATE} , the characteristics of the components of device **50**, the speed at which the power supply Vdd rises and the like.

Hence, an additional mechanism is required for determining when the data at the output of the device **50** is valid for the content of such a cell. It is known in the art to use an additional cell (a reference cell) for determining the exact point in time when a conventional cell becomes valid. It is desired that the data cell become valid before the reference cell, so that the validity of the reference cell indicates the validity of the data cell.

The power up ramp rate primarily affects the speed at which the latch formed of inverters **60** and **62** initially charges capacitor **56** and the speed at which the gate voltage V_{GATE} rises. Since cell **10** (whether as a data or a reference cell) must first overcome the voltage stored on capacitor **56** before device **50** can produce a valid signal, the power up ramp rate affects the ability of the cell to do so. For a given ramp rate, how quickly the cell can overcome the capacitor voltage is a function of the characteristics of the cell, both its charge transfer characteristics and its threshold voltage V_T .

The charge transfer characteristics of a cell are determined according to the cell tunnel width (W) and the cell tunnel length (L). With a low W/L ratio, the cell transfers charge slowly. Alternatively, with a high W/L ratio, the cell transfers charge quickly. Accordingly, in the prior art, the $(W/L)_{DATA}$ ratio of a data cell is set higher than the $(W/L)_{REFERENCE}$ of a reference cell. As a result, the drive current of the reference cells is smaller than the drive current of the data cells and the validity time period of a reference cell is generally longer than the validity time period of a data cell. It is common to set

$$\frac{\left(\frac{W}{L}\right)_{REFERENCE}}{\left(\frac{W}{L}\right)_{DATA}} \approx \frac{2}{3}$$

A cell basically operates in three modes, a cut off mode, a sub-threshold mode and a saturated strong inversion mode.

When the gate voltage V_{GATE} , provided to the cell, is significantly lower than the threshold voltage V_T which

characterizes the cell, the cell is in the cut-off mode. In the cut-off mode, the cell is in a state of high impedance and hence, has substantially no conductivity.

When the gate voltage V_{GATE} , is similar to the threshold voltage V_T (i.e., $|V_{GATE}-V_T|<0.1$ volts), the cell is in the sub-threshold mode. In the sub-threshold mode, the cell is in a state of medium impedance and hence has substantially low conductivity.

When the gate voltage V_{GATE} is higher than the threshold voltage V_T , the cell is in the saturated strong inversion mode. In the saturated strong inversion mode, the cell is in a state of low impedance and hence, has substantially high conductivity. It is noted that conventionally,

$$\frac{I_{SATURATED-STRONG-INVERSION}}{I_{SUB-THRESHOLD}} > 10.$$

It is noted that both the data cell and the reference cell are provided with the same V_{GATE} level (which varies with the power supply ramp rate) but the threshold level of the data cell V_{T-DATA} can be different than the threshold level of the cell V_{T-REF} , due to variations in the manufacturing process, programming states, natural decay over a long period of time, and the like.

When V_{T-REF} is lower than V_{T-DATA} , there is a strong probability that the reference cell will be the first to transform from the sub-threshold stage to the saturated strong inversion stage and become valid (i.e., complete the transfer of the predetermined amount of charge) before the data cell. It is noted that a reference cell with low W/L , in the saturated strong inversion mode, conducts significantly higher currents than a data cell with high W/L in the sub-threshold mode. Thus, depending on the factors described above, the reference cell might indicate that the data cell is valid when this is not the case. It will be appreciated by those skilled in the art that such a situation is totally undesirable.

SUMMARY OF THE PRESENT INVENTION

It is an object of the present invention to provide a device and method which attempts to ensure that, during power-up, reference cells become valid only after data cells do.

There is therefore provided, in accordance with a preferred embodiment of the present invention, an array which includes at least one data cell, at least one cell common line to which the data cell is connected, at least one reference cell, a reference common line to which the reference cell is connected and a voltage differentiator. The voltage differentiator is connected to the cell and reference common lines and receives a powering-up power supply voltage from a power supply. The voltage differentiator provides a reference voltage to the reference common line and a cell voltage to the at least one cell common line, wherein the reference voltage is lower than the cell voltage by a predetermined voltage gap.

Moreover, in accordance with a preferred embodiment of the present invention, the voltage gap is defined as at least twice an expected threshold voltage variation of the cells.

Further, in accordance with a preferred embodiment of the present invention, the voltage differentiator includes first, second and third resistors and first and second current control units. The first resistor R_1 is connected to a powering up voltage source and to the gate of the data cell(s). The second resistor R_2 is connected to the powering-up voltage source and to the gate of the reference cell. The first current control unit is connected between the gate of the data cell

and the ground and conducts an electrical current I_{CELL} therebetween. The second current control unit is connected between the gate of the reference cell and the ground and conducts an electrical current I'_{CELL} therebetween. The third resistor R_3 is connected between the gate of the reference cell and the ground. The first current control unit is further connected to the second current control unit, thereby essentially equating between I'_{CELL} and I_{CELL} .

Still further, in accordance with a preferred embodiment of the present invention, the first current control unit includes a first N-type transistor and a P-type transistor and the second current control unit comprises a second N-type transistor. A source of the first N-type transistor and a source of the second N-type transistor are connected to the ground, a source of the P-type transistor is connected to the data cell, a drain of the second N-type transistor is connected to the reference cell and a gate of the second N-type transistor is connected to a gate and drain of the first N-type transistor and to a gate and drain of the P-type transistor.

Alternatively, in accordance with a preferred embodiment of the present invention, the device includes a voltage moderating unit connected between the voltage differentiator and a gate of the data cell and further connected between the voltage differentiator and a gate of the reference cell. The voltage moderating unit includes a unit which modulates the cell voltage V , thereby providing a moderated cell voltage V' to the gate of the data cell and a unit which modulates the reference voltage V , thereby providing a moderated reference voltage V' to the gate of the reference cell.

There is also provided, in accordance with a preferred embodiment of the present invention, a device for validating the content of at least one data cell. The device includes at least one reference cell, pre-set to be erased, and a voltage differentiator, connected to a gate of the data cell, to a gate of the reference cell and to a powering-up voltage source. The voltage differentiator receives a rising voltage V_{DD} from the powering-up voltage source and provides a first voltage V_{DATA} to the gate of the data cell and a second voltage V_{REF} to the gate of the reference cell. The voltage differentiator maintains the second voltage V_{REF} lower than the first voltage V_{DATA} , by at least a predetermined voltage gap ΔV .

There is also provided, in accordance with a preferred embodiment of the present invention, a method for attempting to ensure that during power up of an array containing at least one latch cell and at least one latch reference cell, the at least one latch reference cell becomes valid after the at least one latch data cell. The method includes the steps of providing a first voltage signal V_{DATA} to the gate of the latch data cell, providing a second voltage signal V_{REF} to the gate of the latch reference cell and maintaining the second voltage signal V_{REF} lower than the first voltage signal V_{DATA} by at least a predetermined voltage gap ΔV .

Further, in accordance with a preferred embodiment of the present invention, the method includes the step of modulating the first voltage signal V_{DATA} and the second voltage signal V_{REF} .

Finally, in accordance with a preferred embodiment of the present invention, the method includes the steps of detecting a flip in the output of the latch of the reference cell and determining the validity of the data cell.

BRIEF DESCRIPTION OF THE DRAWINGS

The present invention will be understood and appreciated more fully from the following detailed description taken in conjunction with the drawings in which:

FIG. 1 is a schematic illustration of a plurality of data cells and a reference cell, known in the art;

FIG. 2 is a schematic illustration of a memory cell and latch device, constructed and operative in accordance with another preferred embodiment of the present invention;

FIG. 3 is a schematic illustration of a device and a memory array, constructed and operative in accordance with a preferred embodiment of the present invention;

FIGS. 4A and 4B are graphical illustrations of a power-up signal and two signals which are functions of the power-up signal;

FIG. 5 is a schematic illustration of a voltage differentiator, constructed and operative in accordance with a further preferred embodiment of the present invention;

FIG. 6 is a schematic illustration of a voltage differentiator, constructed and operative in accordance with another preferred embodiment of the present invention;

FIG. 7A is a voltage versus time diagram, which illustrates the voltage behavior at selected points in device of FIG. 5;

FIG. 7B is an electrical current versus time diagram, which illustrates the electrical current behavior at selected points in device of FIG. 5; and

FIG. 8 is a schematic illustration of a method for operating a validation mechanism, operative in accordance with another preferred embodiment of the present invention.

DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS

The present invention overcome the disadvantages of the prior art by attempting to ensure that, irrespective of the power supply ramp rate and the threshold levels V_T of the reference and data cells, an inversion time $T_{INV-DATA}$ for a data cell is shorter than an inversion time $T_{INV-REF}$ for a reference cell.

Reference is now made to FIG. 3, which is a schematic illustration of a device, generally referenced **100**, and a memory array, constructed and operative in accordance with a preferred embodiment of the present invention. Reference is also made to FIGS. 4A and 4B which graphically illustrate the operation of the device of FIG. 3.

The cell array includes a plurality of cells **150A**, **150B**, **150C**, **150D** and **154**. It is noted that, although not shown, each cell **150** and **154** is connected to a separate memory and latch device such as shown in FIG. 2.

Cell **154** is a reference cell and cells **150A**, **150B**, **150C**, **150D** are the data cells. Furthermore, all of cells **150** and **154** have the same W/L ratio. According to the present invention, reference cell **154** is located on a separate common line than the data cells, so that a different gate voltage can provided thereto. Accordingly, the gate of reference cell **154** is connected to common line **156** and the gates of data cells **150A**, **150B**, **150C**, **150D** are connected to common line **158**.

Device **100** is a voltage differentiator which provides two voltage output signals, V_{CELL} and V_{REF} . V_{CELL} denotes the voltage which is provided to the gate of the data cells (common line **158**) and V_{REF} denotes the voltage which is provided to the gate of the reference cell (common line **156**).

Device **100** includes a voltage source **102** and a differentiator **104** connected thereto. The voltage source **102** produces a voltage signal and provides it to the differentiator **104** which, in turn, produces data and reference gate voltage signals V_{CELL} and V_{REF} , respectively.

As the memory device is powered-up, data gate voltage V_{CELL} rises at a certain rate. According to the invention,

differentiator **100** ensures that reference gate voltage V_{REF} is continuously kept within a substantially fixed voltage difference lower than the V_{CELL} , such that $V_{REF}=V_{CELL}-\Delta V$, where ΔV is substantially constant.

There exist a plurality of criteria for setting the value of ΔV . For example, a conventional cell is characterized by a threshold voltage level V_T which is the point of transition from the sub-threshold mode to the saturated strong inversion mode. V_{T-CELL} denotes the threshold voltage of a data cell and V_{T-REF} denotes the threshold voltage of a reference cell. In the present invention, since the W/L ratio is the same for both types of cells, the threshold levels should be at the same level V_T . However, there is an expected variation in threshold levels of ΔV_T due to production differences, programming and erase cycling, natural decay and the like. Accordingly, it is desirable to set $\Delta V=2\Delta V_T$, so as to ensure that V_{CELL} always reaches V_{T-CELL} before V_{REF} reaches V_{T-REF} .

FIGS. 4A and 4B are voltage vs. time graphs which show the voltage Vdd provided by the power supply, for two different ramp rates, and the resultant signals V_{REF} and V_{CELL} . As discussed hereinabove, the signal V_{REF} remains below the signal V_{CELL} by a fixed amount.

FIGS. 4A and 4B also show the expected inversion voltage V_I of the cells where the inversion voltage V_I is the voltage at which device **50** with an erased cell inverts. The inversion voltage V_I is the voltage at which the inversion time $T_{INVERSION}$ ends and is a function of the threshold voltage V_T of the cell. FIGS. 4A and 4B also show two other inversion voltages V_I' and V_I'' which are below and above desired inversion voltage V_I , respectively, but within the expected variation ΔV .

As can be seen in FIGS. 4A and 4B, if both cells have the same inversion voltage V_I , then the device with the data cell will invert first, since V_{CELL} reaches the inversion voltage V_I first. Thus, FIGS. 4A and 4B show $T_{INV-CELL}$ of the data cells before the inversion time $T_{INV-REF}$ of the reference cell.

If, however, one of the inversion voltages is lower due to a lower threshold voltage, for example at the inversion voltage V_I' , the inversion time T_{INV} for that device will be earlier than its inversion time at inversion voltage V_I . Alternatively, one of the inversion voltages might be higher, for example at the inversion voltage V_I'' . If so, the inversion time T_{INV} for that device will be after its inversion time at inversion voltage V_I . FIGS. 4A and 4B show the corresponding data and reference inversion times $T'_{INV-CELL}$, $T''_{INV-CELL}$, $T'_{INV-REF}$, and $T''_{INV-REF}$.

It is noted that all three data inversion times $T_{INV-CELL}$, $T'_{INV-CELL}$ and $T''_{INV-CELL}$ occur before any reference inversion time $T_{INV-REF}$, $T'_{INV-REF}$ or $T''_{INV-REF}$. Thus, in the present invention, as long as the inversion voltages remain between V_I'' and V_I' (i.e. the difference in threshold voltages of reference and data cells is within the predetermined margin ΔV_T), the device with the data cell will invert before the reference cell.

This relationship is true irrespective of which device has the lower threshold and thus, the lower inversion voltage and irrespective of power supply ramp rate as can be seen when comparing FIGS. 4A and 4B.

Reference is now made to FIG. 5 which is a schematic illustration of a voltage differentiator, generally referenced **300**, constructed and operative in accordance with a further preferred embodiment of the present invention. Differentiator **300** includes three resistors **302** (R_1), **310** (R_2) and **312** (R_3) and two current control units **304** and **306**.

Resistors **302** and **310** are connected to a voltage source (not shown), which provides a voltage signal V_{DD} . Resistor

302 is further connected to current control unit **304** and to an output line **320**. Current control unit **304** is connected to current control unit **306**.

The current control unit **306** is further connected to resistors **310** and **312** and to an output line **322**. Current control units **304** and **306** are further connected to the ground. Resistor **312** is further connected to the ground.

Current control unit **304** maintains a current flow of I_{CELL} and current control unit **306** maintains a current flow I'_{CELL} . According to the present invention, I_{CELL} is substantially equal to I'_{CELL} (i.e., $I_{CELL} \approx I'_{CELL}$). It is noted that, since there is a current flow of I_{R3} through the resistor **312**, hence

$$I_{REF} = I'_{CELL} + I_{R3} > I_{CELL}$$

Resistor **302** has a resistance which is essentially equal to resistor **310**. Accordingly, the voltage gap over the resistor **302** is smaller than the voltage gap over the resistor **310** (i.e., $V_{R1} < V_{R2}$). Thus,

$$V_{CELL} = V_{DD} - V_{R1} \text{ and } V_{REF} = V_{DD} - V_{R2}. \text{ Hence } V_{REF} < V_{CELL}.$$

Reference is now made to FIG. 6 which is a schematic illustration of a voltage differentiator, generally referenced **350**, and a voltage rise moderator, generally referenced **380**, both constructed and operative in accordance with another preferred embodiment of the present invention. Differentiator **350** includes three resistors **352** (R_1), **360** (R_2) and **362** (R_3), two N-type transistors **356** and **358** and a P-type transistor **354**.

Resistors **352** and **360** are connected to a voltage source (not shown) which provides a voltage signal V_{DD} . Resistor **352** is further connected to the source end of transistor **354** and to an output line **370**. The gate and drain of transistor **354** are connected to the gate and drain of transistor **356**, as well as to the gate of transistor **358**.

The drain of transistor **358** is connected to resistors **360** and **362** and to an output line **372**. The source of transistors **356** and **358** are connected to the ground. Resistor **362** is further connected to the ground.

Reference is further made to FIGS. 7A and 7B. FIG. 7A is a voltage versus time diagram which illustrates the voltage behavior at selected points in device **350**. FIG. 7B is an electrical current versus time diagram which illustrates the electrical current behavior at selected points in device **350**.

Transistors **354** and **356** operate as diodes which moderate a current flow I_{CELL} (reference **424** in FIG. 7B) through resistor **352**. Transistor **358**, being gate to gate connected to transistor **356**, maintains a current flow of I'_{CELL} (reference **422** in FIG. 7B) therethrough (it is noted that $I_{CELL} \approx I'_{CELL}$).

The resistor **362** maintains a current flow I_{R3} (reference **428** in FIG. 7B) therethrough. It is noted that I_{R3} is substantially constant but still exhibits a moderate rise over time, which affects I_{REF} . According to the present invention, the resistance of R_2 is set slightly higher than the resistance of R_1 , so as to slightly reduce I_{REF} , thereby compensating for the moderate rise in I_{R3} . Finally we obtain:

$$I_{REF} = I'_{CELL} + I_{R3} > I_{CELL}.$$

Since I_{CELL} and I'_{CELL} rise at approximately at the same rate and I_{R3} is substantially constant, the electrical current gap ΔI (reference **430** in FIG. 7B), is substantially maintained constant.

Through common calculations we obtain that

$$V_{R2} = R_2 I_{REF} = R_2 (I'_{CELL} + I_{R3}) > R_1 I_{CELL} = V_{R1}$$

$$V_{CELL} = V_{DD} - V_{R1} > V_{DD} - V_{R2} = V_{REF}$$

$$V_{CELL} - V_{REF} = V_{R2} - V_{R1} = R_2 (I'_{CELL} + I_{R3}) - R_1 I_{CELL} \\ \approx R_2 I_{R3} = \Delta V$$

With reference to FIG. 7A, reference **402** denotes V_{DD} , reference **404** denotes V_{CELL} , reference **406** denotes V_{REF} and reference **408** denotes the voltage gap ΔV between V_{CELL} and V_{REF} .

Since I_{R3} is substantially constant, hence

$$\Delta V = V_{CELL} - V_{REF} \approx \text{Constant}.$$

It is noted that the method of the present invention is also applicable to verify the content of a cell right after it is programmed or erased, by simulating a power-up procedure.

When the profile of the incoming V_{DD} signal cannot be predicted, there is a probability that the rise of V_{DD} will be too sudden, like a step function. Such a sudden rise proportionally affects the output voltage signals V_{CELL} and V_{REF} . The present invention provides a mechanism which prevents a sudden rise in the voltage signals that are provided to the data cell and the reference cell.

Referring back to FIG. 6, voltage rise moderating unit **380** includes two resistors **382A** and **382B** and two capacitors **384A** and **384B**. Capacitor **384A** is connected between the ground, on one side, and the resistor **382A** and an output line **386**, on the other side. Output line **386** is further connected to a common line which is connected to at least one data cell (not shown). Capacitor **384B** is connected between the ground, on one side, and the resistor **382B** and an output **388**, on the other side. Output **388** is further connected to a common line which is connected to at least one reference cell (not shown). The other end of resistor **382A** is connected to output line **370**, which provides voltage signal V_{CELL} . The other end of resistor **382B** is connected to output line **372**, which provides voltage signal V_{REF} . It is noted that unit **380** is connected between device **350** and the respective cells.

Each of the resistor capacitor pairs acts like a damper for the respective incoming signal. Resistor **382A** and capacitor **384A** act as a damper for voltage signal V_{CELL} , thereby producing an output V'_{CELL} .

Accordingly, even if V_{CELL} rises as a step function, moderator **380** ensures that V'_{CELL} rises more slowly with a moderate slope. The same applies for V_{REF} and V'_{REF} , respectively.

Reference is now made to FIG. 8, which is a schematic illustration of a method for operating a validation mechanism, constructed and operative in accordance with another preferred embodiment of the present invention.

In step **500**, the gate of a data cell is connected to a voltage source which provides a rising voltage V_{CELL} .

In step **502**, the gate of a reference cell is connected to a voltage source which provides rising voltage V_{REF} .

In step **504**, a substantially constant voltage gap ΔV is maintained between V_{CELL} and V_{REF} , wherein $V_{CELL} - V_{REF} \approx \Delta V$.

In step **506**, a flip in the output of the reference cell latch is detected. This flip indicates that the reference cell is valid and further indicates that the data cell is valid.

In step **508**, the validity of the data cell is determined.

It will be appreciated by persons skilled in the art that the present invention is not limited to what has been particularly

shown and described hereinabove. Rather the scope of the present invention is defined only by the claims which follow.

What is claimed is:

1. A semiconductor array comprising:
 - at least one data cell;
 - at least one cell common line to which said at least one data cell is connected;
 - at least one reference cell;
 - a reference common line to which said at least one reference cell is connected; and
 - a voltage differentiator, connected to said cell and reference common lines, for receiving a powering-up power supply voltage from a power supply and for providing a reference voltage to said reference common line and a cell voltage to said at least one cell common line, wherein said reference voltage is lower than said cell voltage by a predetermined voltage gap.
2. The array according to claim 1, wherein said voltage gap is defined as at least twice an expected threshold voltage variation of said cells.
3. The array according to claim 1, wherein said voltage differentiator comprises:
 - a first resistor R_1 , connected to a powering up voltage source and to the gate of said at least one data cell;
 - a second resistor R_2 , connected to said powering-up voltage source and to the gate of said at least one reference cell;
 - a first current control unit connected between said gate of said at least one data cell and the ground, for conducting an electrical current I_{CELL} therebetween;
 - a second current control unit connected between said gate of said at least one reference cell and the ground, conducting an electrical current I'_{CELL} therebetween,
 - a third resistor R_3 , connected between said gate of said at least one reference cell and the ground;
 wherein said first current control unit is further connected to said second current control unit, thereby essentially equating between I'_{CELL} and I_{CELL} .
4. The array according to claim 3, wherein said first current control unit comprises a first N-type transistor and a P-type transistor, and wherein said second current control unit comprises a second N-type transistor,
 - wherein a source of said first N-type transistor and a source of said second N-type transistor are connected to the ground, a source of said P-type transistor is connected to said at least one data cell, a drain of said second N-type transistor is connected to said at least one reference cell, and
 - wherein a gate of said second N-type transistor is connected to a gate and drain of said first N-type transistor and to a gate and drain of said P-type transistor.
5. The array according to claim 1, further comprising a voltage moderating unit, connected between said voltage differentiator and a gate of said at least one data cell, and further connected between said voltage differentiator and a gate of said at least one reference cell,
 - wherein said voltage moderating unit includes means for modulating said cell voltage V , thereby providing a moderated cell voltage V' to said gate of said at least one data cell, and
 - wherein said voltage moderating unit further includes means for modulating said reference voltage V , thereby providing a moderated reference voltage V' to said gate of said at least one reference cell.

6. A device for validating the content of at least one data cell, the device comprising:
 - at least one reference cell, pre-set to be erased, and
 - a voltage differentiator, connected to a gate of said at least one data cell, to a gate of said at least one reference cell and to a powering-up voltage source,
 wherein said voltage differentiator receives a rising voltage V_{DD} from said powering-up voltage source,
 - wherein said voltage differentiator provides a first voltage V_{DATA} to said gate of said at least one data cell and a second voltage V_{REF} to said gate of said at least one reference cell,
 - wherein said voltage differentiator maintains said second voltage V_{REF} lower than said first voltage V_{DATA} , by at least a predetermined voltage gap ΔV .
7. The array according to claim 6, wherein said voltage gap ΔV is determined as at least twice an expected threshold voltage variation of said cells.
8. The array according to claim 6, wherein said voltage differentiator comprises:
 - a first resistor R_1 , connected to a powering-up voltage source and to the gate of said at least one data cell;
 - a second resistor R_2 , connected to said powering-up voltage source and to the gate of said at least one reference cell;
 - a first current control unit connected between said gate of said at least one data cell and the ground, conducting an electrical current I_{CELL} there between;
 - a second current control unit connected between said gate of said at least one reference cell and the ground, for conducting an electrical current I'_{CELL} there between,
 - a third resistor R_3 , connected between said gate of said at least one reference cell and the ground;
 wherein said first current control unit is further connected to said second current control unit, thereby essentially equating between I'_{CELL} and I_{CELL} .
9. The array according to claim 8, wherein said first current control unit comprises a first N-type transistor and a P-type transistor, and wherein said second current control unit comprises a second N-type transistor,
 - wherein a source of said first N-type transistor and a source of said second N-type transistor are connected to the ground, a source of said P-type transistor is connected to said at least one data cell, a drain of said second N-type transistor is connected to said at least one reference cell, and
 - wherein a gate of said second N-type transistor is connected to a gate and drain of said first N-type transistor and to a gate and drain of said P-type transistor.
10. The array according to claim 6, further comprising a voltage moderating unit, connected between said voltage differentiator and a gate of said at least one data cell, and further connected between said voltage differentiator and a gate of said at least one reference cell,
 - wherein said voltage moderating unit includes means for modulating said cell voltage V , thereby providing a moderated cell voltage V' to said gate of said at least one data cell, and
 - wherein said voltage moderating unit further includes means for modulating said reference voltage V , thereby providing a moderated reference voltage V' to said gate of said at least one reference.
11. In an array containing at least one latch cell and at least one latch reference cell, a method for attempting to

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ensure that during power up, the at least one latch reference cell becomes valid after the at least one latch data cell, the method comprising the steps of:

- providing a first voltage signal V_{DATA} to the gate of said at least one latch data cell;
- providing a second voltage signal V_{REF} to the gate of said at least one latch reference cell; and
- maintaining said second voltage signal V_{REF} lower than said first voltage signal V_{DATA} by at least a predetermined voltage gap ΔV .

12. The method according to claim **11**, further comprising the step of modulating said first voltage signal V_{DATA} and said second voltage signal V_{REF} .

13. In an array containing at least one latch cell and at least one latch reference cell, a method for determining the validity of the at least one latch data cell during power up, the method comprising the steps of:

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providing a first voltage signal V_{DATA} to the gate of said at least one latch data cell;

providing a second voltage signal V_{REF} to the gate of said at least one latch reference cell;

maintaining a said second voltage signal V_{REF} lower than said first voltage signal V_{DATA} by at least a predetermined voltage gap ΔV ;

detecting a flip in the output of the latch of said at least one reference cell; and

determining the validity of said at least one data cell.

14. The method according to claim **13**, further comprising the step of modulating said first voltage signal V_{DATA} and said second voltage signal V_{REF} .

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